

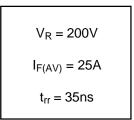
### HFB25HJ20

#### **FRED**

### Ultrafast, Soft Recovery Diode

#### **Features**

- · Reduced RFI and EMI
- · Reduced Snubbing
- Extensive Characterization of Recovery Parameters
- Hermetic
- Surface Mount



#### **Description**

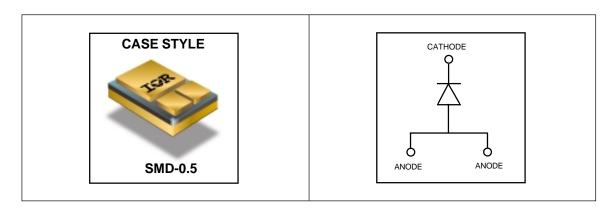
These Ultrafast, soft recovery diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

### **Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_R$	Cathode to Anode Voltage	200	V
I <sub>F(AV)</sub>	Continuous Forward Current, ⊕ T <sub>C</sub> = 106°C	25	Δ
I <sub>FSM</sub>	Single Pulse Forward Current, ② T <sub>C</sub> = 25°C	150	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation	70	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to +150	°C

Note: ① D.C. = 50% rect. wave

② 1/2 sine wave, 60 Hz , P.W. = 8.33 ms





## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions
V <sub>BR</sub>	Cathode Anode Breakdown Voltage	200	_	_	V	$I_R = 100 \mu A$
V <sub>F</sub>	Forward Voltage	_	_	1.18		I <sub>F</sub> = 25A, T <sub>J</sub> =-55°C
	See Fig. 1	_	_	0.94		I <sub>F</sub> = 10A, T <sub>J</sub> = 25°C
		_	_	1.07	V	I <sub>F</sub> = 25A, T <sub>J</sub> = 25°C
		_	_	1.19		I <sub>F</sub> = 50A, T <sub>J</sub> = 25°C
		_	_	0.88		I <sub>F</sub> = 25A, T <sub>J</sub> =125°C
I <sub>R</sub>	Reverse Leakage Current	_	_	10	μA	$V_R = V_R$ Rated
	See Fig. 2	_	_	250	μA	V <sub>R</sub> = V <sub>R</sub> Rated, T <sub>J</sub> = 125°C
Ст	Junction Capacitance, See Fig. 3	_	_	78	pF	V <sub>R</sub> = 200V
Ls	Series Inductance	_	4.8	_	nΗ	Measured from center of cathod
						pad to center of anode pad

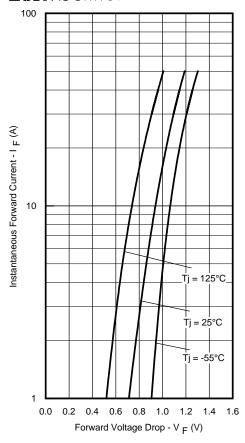
## Dynamic Recovery Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions		
t <sub>rr</sub>	Reverse Recovery Time	_	—	35	ns	$I_F = 1.0A, V_R = 30V, di_f/dt = 200A/\mu s$		
t <sub>rr1</sub>	Reverse Recovery Time	_	28	_	ns	T <sub>J</sub> = 25°C	See Fig.	
t <sub>rr2</sub>		_	43	l		$T_J = 125$ °C	5	$I_{F} = 25A$
I <sub>RRM1</sub>	Peak Recovery Current	_	3.9	_	A	$T_J = 25^{\circ}C$	See Fig.	
I <sub>RRM2</sub>		_	6.1			$T_J = 125$ °C	6	$V_{R} = 160V$
Q <sub>rr1</sub>	Reverse Recovery Charge	_	61	-	nC	$T_J = 25^{\circ}C$	See Fig.	
Q <sub>rr2</sub>		_	146		''	$T_J = 125$ °C	7	$di_f/dt = 200A/\mu s$
di <sub>(rec)M</sub> /dt1	Peak Rate of Fall of Recovery Current	_	820		A/us	T <sub>J</sub> = 25°C	See Fig.	
di <sub>(rec)M</sub> /dt2	During t <sub>b</sub>	-	1560	_	Α,μ3	T <sub>J</sub> = 125°C	8	

### **Thermal - Mechanical Characteristics**

	Parameter	Тур.	Max.	Units
R <sub>thJC</sub>	Junction-to-Case	_	1.76	°C/W
Wt	Weight	1.0	_	g

# International TOR Rectifier



**Fig. 1** - Maximum Forward Voltage Drop Vs. Instantaneous Forward Current

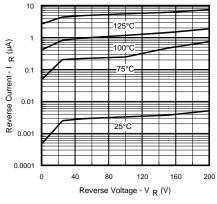
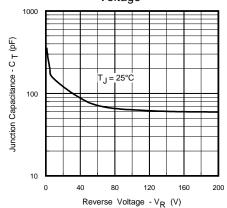


Fig. 2 - Typical Reverse Current Vs. Reverse Voltage



**Fig. 3** - Typical Junction Capacitance Vs. Reverse Voltage

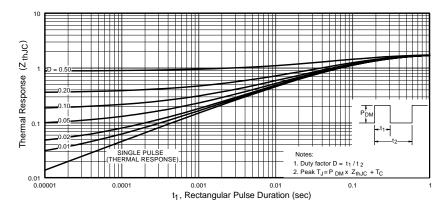


Fig. 4 - Maximum Thermal Impedance  $Z_{\text{thjc}}$  Characteristics

## HFB25HJ20

# International Rectifier

1000

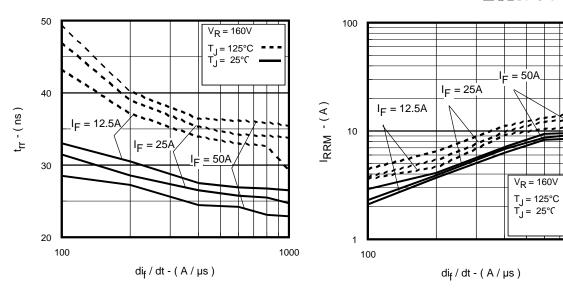


Fig. 5 - Typical Reverse Recovery Vs. dif/dt,

Fig. 6 - Typical Recovery Current Vs. di<sub>f</sub>/dt,

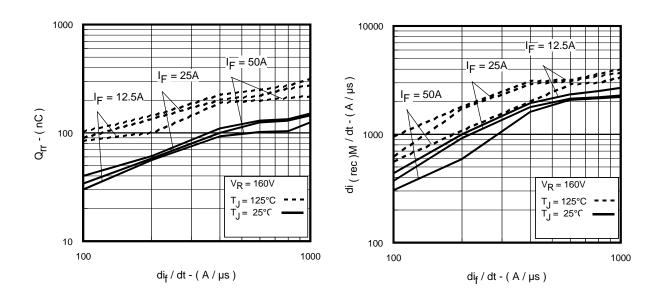


Fig. 7 - Typical Stored Charge Vs. di<sub>f</sub>/dt

Fig. 8 - Typical di<sub>(rec)M</sub>/dt Vs. di<sub>f</sub>/dt

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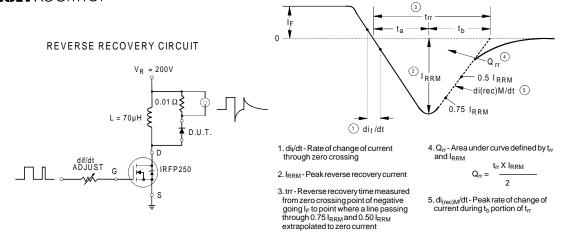
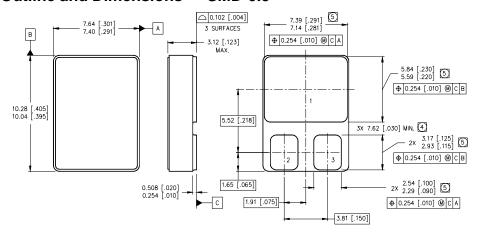


Fig. 9 - Reverse Recovery Parameter Test Circuit

Fig. 10 - Reverse Recovery Waveform and Definitions

### Case Outline and Dimensions — SMD-0.5



NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- (4) DIMENSION INCLUDES METALLIZATION FLASH.
- DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

- 1 = CATHODE
- 2 = COMMON ANODE
- 3 = COMMON ANODE

International

TOR Rectifier

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